

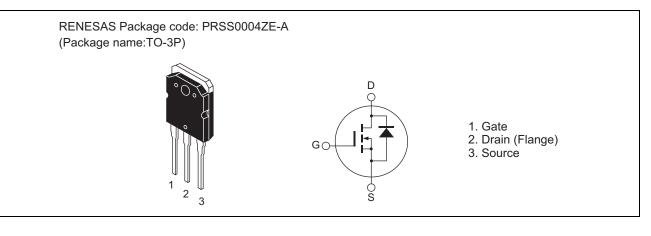
# RJL5018DPK

Silicon N Channel MOS FET High Speed Power Switching

## Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

## Outline



## **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	500	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	35	А
Drain peak current	Note1 D (pulse)	105	А
Body-drain diode reverse drain current	I <sub>DR</sub>	35	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	105	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	9	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	4.5	mJ
Channel dissipation	Pch Note2	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

3. STch = 25°C, Tch  $\leq$  150°C

REJ03G1817-0100 Rev.1.00 Sep 11, 2009

## **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

ltem	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	500	_	_	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μA	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μA	$V_{GS}$ = ±30 V, $V_{DS}$ = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.5	_	4.0	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA
Static drain to source on state	R <sub>DS(on)</sub>	_	0.14	0.17	Ω	$I_D$ = 17.5 A, $V_{GS}$ = 10 V <sup>Note4</sup>
resistance						
Input capacitance	Ciss	—	3790	—	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	410	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	49	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	42	_	ns	I <sub>D</sub> = 17.5 A
Rise time	tr	_	72	_	ns	$V_{GS}$ = 10 V R <sub>L</sub> = 14.3 Ω Rg = 10 Ω
Turn-off delay time	t <sub>d(off)</sub>	_	162	_	ns	
Fall time	t <sub>f</sub>	_	111		ns	
Total gate charge	Qg	_	98	_	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	_	17.6	_	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 35 A
Gate to drain charge	Qgd	_	42.3		nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.95	1.60	V	$I_F = 35 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		170	_	ns	I <sub>F</sub> = 35 A, V <sub>GS</sub> = 0
						di⊧/dt = 100 A/µs

Notes: 4. Pulse test

## Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	
TO-3P	SC-65	PRSS0004ZE-A	TO-3P / TO-3PV	5.0g	Linite and
	<u>1.6</u> <u>1.4 Ma</u>	15.6 ± 0.3	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		
	<u>5.45 ± 0</u>		<u>0</u> <u>0</u> <u>■</u> <u>5.45 ± 0.5</u>		

## **Ordering Information**

Part No.	Quantity	Shipping Container
RJL5018DPK-00-T0	360 pcs	Box (Tube)

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